

6-rows 85 mA LEDs driver with boost regulator for LCD panels backlight

Datasheet - production data



Features

- Boost section
 - 4.5 V to 36 V input voltage range
 - Internal power MOSFET
 - Internal +5 V LDO for device supply
 - Up to 36 V output voltage
 - Constant frequency peak current-mode control
 - 250 kHz to 1 MHz adjustable switching frequency
 - External synchronization for multi-device application
 - Pulse-skip power saving mode at light load
 - Programmable soft-start
 - Programmable OVP protection
 - Stable with ceramic output capacitors
 - Thermal shutdown
- · Backlight driver section
 - Six rows with 85 mA maximum current capability (adjustable)
 - Rows disable option
 - Less than 10 µs minimum dimming on-time
 - ±2% current matching between rows
 - LED failure (open and short-circuit) detection

Applications

- · LCD monitors and TV panels
- PDAs panel backlight
- · GPS panel backlight

Description

The LED7707 consists of a high efficiency monolithic boost converter and six controlled current generators (rows) specifically designed to supply LED arrays used in the backlighting of LCD panels. The device can manage an output voltage up to 36 V (i.e. 10 white LEDs per row).

The generators can be externally programmed to sink up to 85 mA and can be dimmed via a PWM signal (1% dimming duty-cycle at 1 kHz can be managed). The device can detect and manage open circuit and short-circuit LED faults and leave unused rows floating. Basic protections (output overvoltage, internal MOSFET overcurrent and thermal shutdown) are provided.

Table 1. Device summary

Order code	Package	Packing
LED7707	VFQFPN-24 4x4 (exposed pad)	Tube
LED7707TR	VEGETN-24 4x4 (exposed pad)	Tape and reel

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1 Typical application circuit

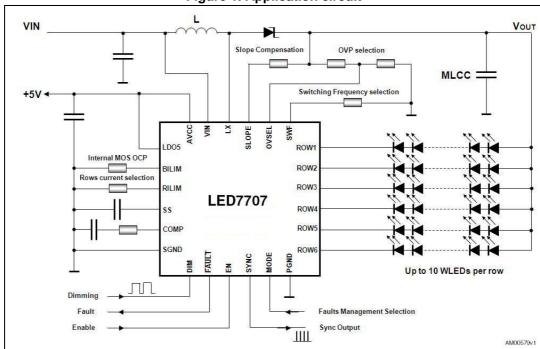


Figure 1. Application circuit



LED7707 Pin settings

2 Pin settings

2.1 Connections

COMP **OVSEL RILIM PGND** ROW6 **BILIM LED7706** ROW5 **FSW** MODE ROW4 **AVCC** ROW3 SLOPE SGND ROW2

Figure 2. Pin connection (through top view)

2.2 Pin description

Table 1. Pin functions

N°	Pin	Function
1	COMP	Error amplifier output. A simple RC series between this pin and ground is needed to compensate the loop of the boost regulator.
2	RILIM	Output generators current limit setting. The output current of the rows can be programmed connecting a resistor to SGND.
3	BILIM	Boost converter current limit setting. The internal MOSFET current limit can be programmed connecting a resistor to SGND.
4	FSW	Switching frequency selection and external sync input. A resistor to SGND is used to set the desired switching frequency. The pin can also be used as external synchronization input. See Section 5.1.5 on page 16 for details.
5	MODE	Current generators fault management selector. It allows to detect and manage LEDs failures. See Section 5.3.2 on page 24 for details.
6	AVCC	+ 5 V analog supply. Connect to LDO5 through a simple RC filter.
7	LDO5	+ 5 V LDO output and power section supply. Bypass to SGND with a 1 μF ceramic capacitor.



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Pin settings LED7707

Table 1. Pin functions (continued)

N°	Pin	Function
8	VIN	Input voltage. Connect to the main supply rail.
9	SLOPE	Slope compensation setting. A resistor between the output of the boost converter and this pin is needed to avoid sub-harmonic instability. Refer to Section 6.1 on page 27 for details.
10	SGND	Signal ground. Supply return for the analog circuitry and the current generators.
11	ROW1	Row driver output #1.
12	ROW2	Row driver output #2.
13	ROW3	Row driver output #3.
14	ROW4	Row driver output #4.
15	ROW5	Row driver output #5.
16	ROW6	Row driver output #6.
17	PGND	Power ground. Source of the internal power MOSFET.
18	OVSEL	Overvoltage selection. Used to set the desired 0 V threshold by an external divider. See Section 5.1.4 on page 16 for details.
19	LX	Switching node. Drain of the internal power MOSFET.
20	DIM	Dimming input. Used to externally set the brightness by using a PWM signal.
21	EN	Enable input. When low, the device is turned off. If tied high or left open, the device is turned on and a soft-start sequence takes place.
22	FAULT	Fault signal output. Open drain output. The pin goes low when a fault condition is detected (see Section 5.3.1 on page 23 for details).
23	SYNC	Synchronization output. Used as external synchronization output.
24	SS	Soft-start. Connect a capacitor to SGND to set the desired soft-start duration.

LED7707 Electrical data

3 Electrical data

3.1 Maximum ratings

Table 2. Absolute maximum ratings (1)

Symbol	Parameter	Value	Unit
V _{AVCC}	AVCC to SGND	-0.3 to 6	
V _{LDO5}	LDO5 to SGND	-0.3 to 6	
	PGND to SGND	-0.3 to 0.3	
V _{IN}	VIN to PGND	-0.3 to 40	
V _{LX}	LX to SGND	-0.3 to 40	
	LX to PGND	-0.3 to 40	V
	RILIM, BILIM, SYNC, OVSEL, SS to SGND	-0.3 to V _{AVCC} + 0.3	1
	EN, DIM, SW, MODE, FAULT to SGND	-0.3 to 6	
	ROWx to PGND/ SGND	-0.3 to 40	
	SLOPE to VIN	V _{IN} - 0.3 to V _{IN} + 6	
	SLOPE to SGND	-0.3 to 40	
	Internal switch maximum RMS current (flowing through LX node)	2.0	А
P _{TOT}	Power dissipation @ T _A = 25 °C	2.3 ⁽²⁾	W
	Maximum withstanding voltage range test condition: CDF-AEC-Q100-002- "human body model" acceptance criteria: "normal performance"	±1000	٧

Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the
device. Exposure to absolute maximum rated conditions for extended periods may affect device reliability.

3.2 Thermal data

Table 3. Thermal data

Symbol	Parameter	Value	Unit
R _{thJA}	Thermal resistance junction-to-ambient	42	°C/W
T _{STG}	Storage temperature range	-50 to 150	°C
T _J	Junction operating temperature range	-40 to 150	°C

^{2.} Power dissipation referred to the device mounted on the demonstration board described in section 5.5.

Electrical characteristics LED7707

4 Electrical characteristics

 V_{IN} = 12 V; T_J = 25 °C and LDO5 connected to AVCC if not otherwise specified $^{\rm (a)}$

Table 4. Electrical characteristics

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit		
Supply section								
V _{IN}	Input voltage range		4.5		36	V		
V _{BST}	Boost section output voltage				36	V		
V_{LDO5}	LDO output and IC supply voltage	EN high	4.4	5	5.5	V		
V _{AVCC}	LDO output and to supply voltage	$I_{LDO5} = 0 \text{ mA}$	4.4	3	5.5	V		
I _{IN,Q}	Operating quiescent current	R_{RILIM} = 51 kW, R_{BILIM} = 220 kW, R_{SLOPE} = 680 kW, DIM tied to SGND		1		mA		
I _{IN,SHDN}	Operating current in shutdown	EN low		20	30	mA		
V _{UVLO,ON}	LDO5 under voltage lock out upper threshold			4.0	4.3	V		
V _{UVLO,OFF}	LDO5 under voltage lock out lower threshold		3.5	3.7		V		
LDO linear	regulator							
	Line regulation	$6 \text{ V} \le \text{V}_{\text{IN}} \le 36 \text{ V}, \text{I}_{\text{LDO5}} = 30 \text{ mA}$			30			
	LDO dropout voltage	$I_{LDO5} = 10 \text{ mA (-10% drop)}$		80	120	mV		
	LDO maximum autaut aurrant	V _{LDO5} > V _{UVLO,ON}	25	40	60	mA		
	LDO maximum output current	V _{LDO5} < V _{UVLO,OFF}		20	30			
Boost secti	on							
t _{ON,min}	Minimum switching on-time				200	ns		
f _{SW}	Default switching frequency	FSW connected to AVCC	570	660	770	1.11=		
	Minimum FSW sync frequency			220		kHz		
	FSW sync input low level		240					
	FSW sync input high level				350	mV		
	FSW sync input hysteresis			30				
	FSW sync min ON time				270	%		
	SYNC output duty-cycle	FSW connected to AVCC (Internal oscillator selected)		34	40	%		



a. Specification referred to T $_J$ from 0 °C to +85 °C. Specification over the 0 to +85 °C T $_J$ range are assured by design, characterization and statistical correlation.

Table 4. Electrical characteristics

SYNC output high level I _{SYNC} = 10 mA	Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
Note		SYNC output high level	I _{SYNC} = 10 mA				mV
K _B		SYNC output low level	I _{SYNC} = -10 mA			20	
KB LX current coefficient RBILIM = 600 kW 1X10* 06* 06* 0 0 V RDS(on) Internal MOSFET on-resistance 280 500 mW OC and OV protections VTH, OVP Overvoltage protection reference threshold 1.145 V Soft-start and power management EN, turn-on threshold 0.8 — V EN, turn-off threshold 0.8 — — DIM, high level threshold 1.3 — — EN, pull-up current 2.5 — mA SS, charge current 4 5 6 MA SS, reduced switching frequency release threshold 0.8 V Current generators section KR Current generators gain 1850 V ΔKR _R (1) Current generators gain accuracy ±2.0 % V _{1FB} Feedback regulation voltage 700 750 mV V _{rows} , FAULT FAULT pin low-level voltage I _{FAULT,SINK} = 4 mA 250 380 <td>Power swit</td> <td>ch</td> <td>,</td> <td>'</td> <td></td> <td></td> <td>l</td>	Power swit	ch	,	'			l
OC and OV protections	K _B	LX current coefficient	R _{BILIM} = 600 kW	1 x 10 ⁶	1.2 X 1 0 ⁶		V
V _{TH,OVP} Overvoltage protection reference threshold 1.145 V Soft-start and power management EN, turn-on threshold 0.8 1.6 EN, turn-off threshold 0.8 V DIM, high level threshold 1.3 0.8 EN, pull-up current 2.5 mA SS, charge current 4 5 6 SS, end-of-startup threshold 1.8 2.4 2.6 SS, reduced switching frequency release threshold 0.8 V Current generators section K _R Current generators gain 1850 V ΔK _R (1) Current generators gain accuracy ±2.0 % V _{FB} Feedback regulation voltage 700 750 mV V _{rowx} , FAULT ED short-circuit detection threshold MODE tied to SGND 4.0 V V _{FAULT} , LOW FAULT pin low-level voltage I _{FAULT,SINK} = 4 mA 250 380 mV Thermal shutdown turn-off temperature 150 °C	R _{DS(on)}	Internal MOSFET on-resistance			280	500	mW
Variable Variable	OC and OV	protections					
EN, turn-on threshold 0.8	$V_{TH,OVP}$				1.145		V
EN, turn-off threshold 0.8	Soft-start a	nd power management			•	•	
DIM, high level threshold DIM, low level threshold DIM, pull-up current DIM,		EN, turn-on threshold				1.6	
DIM, high level threshold 1.3 0.8		EN, turn-off threshold		0.8			
EN, pull-up current 2.5		DIM, high level threshold		1.3			V
SS, charge current 4 5 6 mA		DIM, low level threshold				0.8	
SS, charge current 4 5 6 SS, end-of-startup threshold 1.8 2.4 2.6 SS, reduced switching frequency release threshold 0.8 V Current generators section		EN, pull-up current			2.5		•
SS, reduced switching frequency release threshold Current generators section K _R Current generators gain 1850 V ΔK _R ⁽¹⁾ Current generators gain accuracy ±2.0 % V _{IFB} Feedback regulation voltage 700 750 mV V _{rowx, FAULT} LED short-circuit detection threshold MODE tied to SGND 4.0 V V _{FAULT, LOW} FAULT pin low-level voltage I _{FAULT,SINK} = 4 mA 250 380 mV Thermal shutdown T _{SHDN} Thermal shutdown turn-off temperature		SS, charge current		4	5	6	mA
Current generators section K _R Current generators gain 1850 V ΔK _R ⁽¹⁾ Current generators gain accuracy ±2.0 % V _{IFB} Feedback regulation voltage 700 750 mV V _{rowx, FAULT} LED short-circuit detection threshold HAULT, SINK = 4 mA 250 380 mV Thermal shutdown T _{SHDN} Thermal shutdown turn-off temperature 150 c°C		SS, end-of-startup threshold		1.8	2.4	2.6	
$\begin{array}{c ccccccccccccccccccccccccccccccccccc$					0.8		V
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	Current ge	nerators section	,	'			l
VIFB Feedback regulation voltage 700 750 mV Vrowx, FAULT LED short-circuit detection threshold MODE tied to SGND 4.0 V VFAULT, LOW FAULT pin low-level voltage IFAULT,SINK = 4 mA 250 380 mV Thermal shutdown TSHDN Thermal shutdown turn-off temperature 150 °C	K _R	Current generators gain			1850		V
V _{rowx} , F _{AULT} LED short-circuit detection threshold MODE tied to SGND 4.0 V V _{FAULT} , Low FAULT pin low-level voltage I _{FAULT,SINK} = 4 mA 250 380 mV Thermal shutdown T _{SHDN} Thermal shutdown turn-off temperature 150 °C	ΔK _R ⁽¹⁾	Current generators gain accuracy				±2.0	%
Thermal shutdown Thermal shutdown To Thermal shutdown	V _{IFB}	Feedback regulation voltage			700	750	mV
Thermal shutdown Thermal shutdown Thermal shutdown turn-off temperature			MODE tied to SGND		4.0		V
T _{SHDN} Thermal shutdown turn-off temperature 150 °C		FAULT pin low-level voltage	I _{FAULT,SINK} = 4 mA		250	380	mV
T _{SHDN} turn-off temperature 150 °C	Thermal sh	utdown		·			
	T _{SHDN}				150		°C
		Thermal shutdown hysteresis			30		•

^{1.} $I_{ROW} = K_R / R_{RILIM}$, DI_{ROW} / I_{ROW} » $DK_R / K_R + DR_{RILIM} / R_{RILIM}$



Operation description LED7707

5 Operation description

The device can be divided into two sections: the boost section and the backlight driver section. These sections are described in the next paragraphs.

Figure 3 provides an overview of the internal blocks of the device.

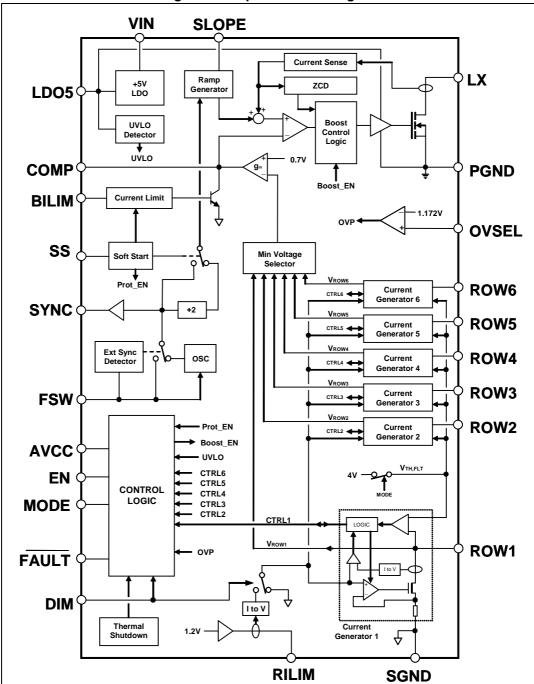


Figure 3. Simplified block diagram



5.1 **Boost section**

5.1.1 **Functional description**

The LED7707 is a monolithic LEDs driver for the backlight of LCD panels and it consists of a boost converter and six PWM-dimmable current generators.

The boost section is based on a constant switching frequency, peak current-mode architecture. The boost output voltage is controlled such that the lowest row's voltage, referred to SGND, is equal to an internal reference voltage (700 mV typ.). The input voltage range is from 4.5 V up to 36 V. In addition, the LED7707 has an internal LDO that supplies the internal circuitry of the device and is capable to deliver up to 40 mA. The input of the LDO is the VIN pin.

The LDO5 pin is the LDO output and the supply for the power MOSFET driver at the same time. The AVCC pin is the supply for the analog circuitry and should be connected to the LDO output through a simple RC filter in order to improve the noise rejection.

VIN LDO5 LDO Rfilt **LED7707** AVCC Cavcc CLDO5 100nF 1uF SGND

Figure 4. AVCC filtering

Two loops are involved in regulating the current sunk by the generators.

The main loop is related to the boost regulator and uses a constant frequency peak currentmode architecture to regulate the power rail that supplies the LEDs (Figure 5), while an internal current loop regulates the same current (flowing through the LEDs) at each row according to the set value (RILIM pin).

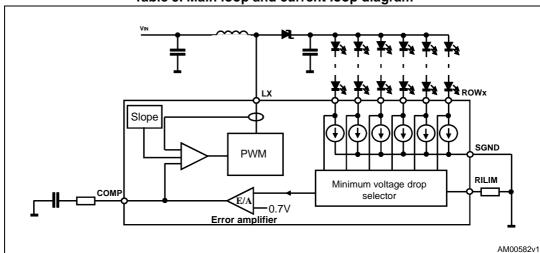


Table 5. Main loop and current loop diagram

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A dedicated circuit automatically selects the lowest voltage drop among all the rows and provides this voltage to the main loop that, in turn, regulates the output voltage. In fact, once the reference generator has been detected, the error amplifier compares its voltage drop to the internal reference voltage and varies the COMP output. The voltage at the COMP pin determines the inductor peak current at each switching cycle. The output voltage of the boost regulator is thus determined by the total forward voltage of the LEDs strings (see *Figure 5*):

Equation 1

$$V_{BST} = \max_{i=1}^{N_{ROWS}} \left(\sum_{j=1}^{M_{LEDS}} V_{F,j} \right) + 700 \text{mV}$$

where the first term represents the highest total forward voltage drop over N active rows and the second is the voltage drop across the leading generator (700 mV typ.).

The device continues to monitor the voltage drop across all the rows and automatically switches to the current generator having the lowest voltage drop.

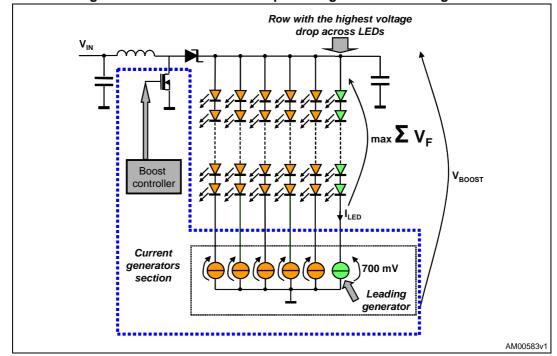


Figure 5. Calculation of the output voltage of the boost regulator

5.1.2 Enable function

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The LED7707 is enabled by the EN pin. This pin is active high and, when forced to SGND, the device is turned off. This pin is connected to a permanently active 2.5 μ A current source; when sudden device turn-on at power-up is required, this pin must be left floating or connected to a delay capacitor. Starting from an ON state, when the LED7707 is turned off, it quickly discharges the Soft-Start capacitor and turns off the power-MOSFET, the current generators and the LDO. The power consumption is thus reduced to 20 μ A only.

In applications where the dimming signal is used to turn on and off the device, the EN pin can be connected to the DIM pin as shown in *Figure 6*.

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DIM BAS69 EN LED7707
220k 100n SGND

Figure 6. External sync waveforms

5.1.3 Soft-start

The soft-start function is required to perform a correct start-up of the system, controlling the inrush current required to charge the output capacitor and to avoid output voltage overshoot. The soft-start duration is set connecting an external capacitor between the SS pin and ground. This capacitor is charged with a 5 mA (typ.) constant current, forcing the voltage on the SS pin to ramp up. When this voltage increases from zero to nearly 1.2 V, the current limit of the power MOSFET is proportionally released from zero to its final value. However, because of the limited minimum on-time of the switching section, the inductor might saturate due to current runaway. To solve this problem the switching frequency is reduced to one half of the nominal value at the beginning of the soft-start phase. The nominal switching frequency is restored after the SS pin voltage has crossed 0.8 V.

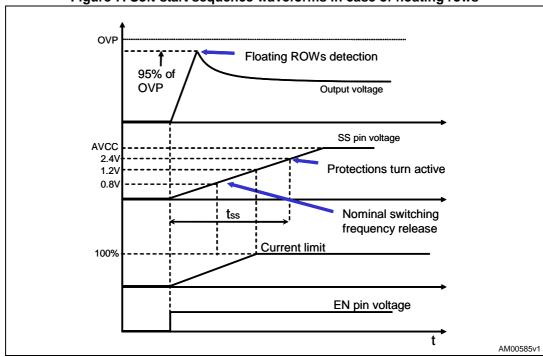


Figure 7. Soft-start sequence waveforms in case of floating rows

During the soft-start phase the floating rows detection is also performed. In presence of one or more floating rows, the voltage across the involved current generator drops to zero. This voltage becomes the inverting input of the error amplifier through the minimum voltage drop selector (see *Figure 5*). As a consequence the error amplifier is unbalanced and the loop

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reacts by increasing the output voltage. When it reaches the floating row detection (FRD) threshold (which coincides with the OVP threshold, see Section 5.1.4), the floating rows are managed according to Table 5 (see Section 5.3 on page 23). After the SS voltage reaches a 2.4 V threshold, the start-up finishes and all the protections turn active. The soft-start capacitor C_{SS} can be calculated according to equation 2.

Equation 2

$$C_{SS} \cong \frac{I_{SS} \cdot t_{SS}}{2.4}$$

Where $I_{SS} = 5 \mu A$ and t_{SS} is the desired soft-start duration.

5.1.4 Overvoltage protection

An adjustable overvoltage protection is available. It can be set feeding the OVSEL pin with a partition of the output voltage. The voltage of the central tap of the divider is thus compared to a fixed 1.145 V threshold. When the voltage of the OVSEL pin exceeds the OV threshold, the switching activity is suspended. It is resumed as OVSEL returns below the OV threshold. A 10 mV hysteresis is provided. No device turn-off is performed. Normally, the value of the high-side resistors of the divider is in the order of 100 k Ω to reduce the output capacitor discharge when the boost converter is off (during the off phase of the dimming cycle), whereas the low-side resistor can be calculated as:

Equation 3

$$R_2 = R_1 \cdot \frac{1.145V}{V_{OUT.MAX} + 4V - 1.145V}$$

An additional filtering capacitor C_F (typically in the 100 pF - 330 pF range) may be required to improve noise rejection at the OVSEL pin (see *Figure 8*).

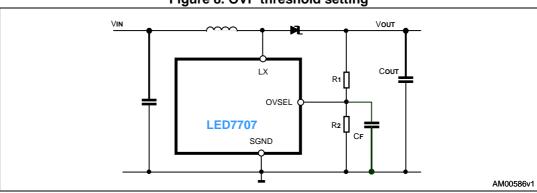


Figure 8. OVP threshold setting

5.1.5 Switching frequency selection and synchronization

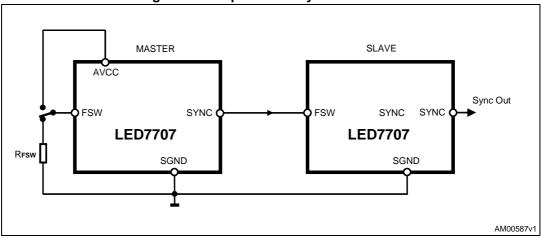
The switching frequency of the boost converter can be set in the 250 kHz-1 MHz range by connecting the FSW pin to ground through a resistor. Calculation of the setting resistor is made using equation 4 and should not exceed the 100 k Ω - 400 k Ω range.

Equation 4

$$R_{FSW} = \frac{F_{SW}}{2.5}$$

In addition, when the FSW pin is tied to AVCC, the LED7707 uses a default 660 kHz fixed switching frequency, allowing to save a resistor in minimum component-count applications.

Figure 9. Multiple device synchronization



The FSW pin can also be used as synchronization input, allowing the LED7707 to operate both as master or slave device. If a clock signal with a 220 kHz minimum frequency is applied to this pin, the device locks synchronized. The signal provided to the FSW pin must cross the 270 mV threshold in order to be recognized. The minimum pulse width which allows the synchronizing pulses to be detected is 270 ns. An internal time-out allows synchronization as long as the external clock frequency is greater than 220 kHz.

Keeping the FSW pin voltage lower than 270 mV for more than 4.5 μ s results in a stop of the device switching activity. Normal operation is resumed as soon as FSW rises above the mentioned threshold and the soft-start sequence is repeated.

The SYNC pin is a synchronization output and provides a 35 % (typ.) duty-cycle clock when the LED7707 is used as master or a replica of the FSW pin when used as slave. It is used to connect multiple devices in a daisy-chain configuration or to synchronize other switching converters running in the system with the LED7707 (master operation). When an external synchronization clock is applied to the FSW pin, the internal oscillator is over-driven: each switching cycle begins at the rising edge of clock, while the slope compensation (*Figure 10*) ramp starts at the falling edge of the same signal. Thus, to prevent sub-harmonic instability (see *Section 5.1.6*), the external synchronization clock is required to have a 40 % maximum duty-cycle when the boost converter is working in continuous-conduction mode (CCM) in order to assure that the slope compensation is effective (starts with duty-cycle lower than 40%)



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Operation description LED7707

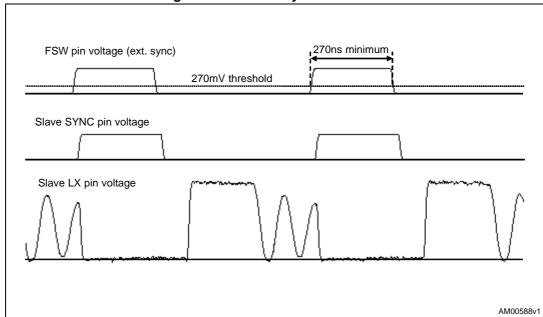


Figure 10. External sync waveforms

5.1.6 Slope compensation

The constant frequency, peak current-mode topology has the advantage of very easy loop compensation with output ceramic caps (reduced cost and size of the application) and fast transient response. In addition, the intrinsic peak-current measurement simplifies the current limit protection, avoiding undesired saturation of the inductor.

On the other side, this topology has a drawback: there is an inherent open loop instability when operating with a duty-ratio greater than 0.5. This phenomenon is known as "Sub-Harmonic Instability" and can be avoided by adding an external ramp to the one coming from the sensed current. This compensating technique, based on the additional ramp, is called "slope compensation". In *Figure 11*, where the switching duty-cycle is higher than 0.5, the small perturbation DI_L dies away in subsequent cycles thanks to the slope compensation and the system reverts to a stable situation.

The SLOPE pin allows to properly set the amount of slope compensation connecting a simple resistor R_{SLOPE} between the SLOPE pin and the output. The compensation ramp starts at 35% (typ.) of each switching period and its slope is given by the following equation:

Equation 5

$$S_{E} = K_{S} \left(\frac{V_{OUT} - V_{IN} - V_{BE}}{R_{SLOPE}} \right)$$

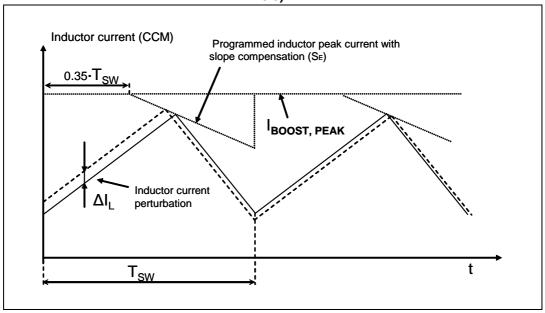
Where $K_S = 5.8 \times 10^{10} \text{ s}^{-1}$, $V_{BE} = 2 \text{ V}$ (typ.) and S_E is the slope ramp in [A/s].

To avoid sub-harmonic instability, the compensating slope should be at least half the slope of the inductor current during the off-phase when the duty-cycle is greater than 50%. The value of R_{SLOPE} can be calculated according to equation 6.

Equation 6

$$R_{SLOPE} \le \frac{2 \cdot K_S \cdot L \cdot (V_{OUT} - V_{IN} - V_{BE})}{(V_{OUT} - V_{IN})}$$

Figure 11. Effect of slope compensation on small inductor current perturbation (D> 0.5)



5.1.7 Boost current limit

The design of the external components, especially the inductor and the flywheel diode, must be optimized in terms of size relying on the programmable peak current limit. The LED7707 improves the reliability of the final application giving the way to limit the maximum current flowing into the critical components. A simple resistor connected between the BILIM pin and ground sets the desired value. The voltage at the BILIM pin is internally fixed to 1.23 V and the current limit is proportional to the current flowing through the setting resistor, according to the following equation:

Equation 7

$$I_{BOOST,PEAK} = \frac{K_B}{R_{BILIM}}$$

where

$$K_{B} = 1.2 \cdot 10^{6} V$$

The maximum allowed current limit is 5 A, resulting in a minimum setting resistor $R_{BILIM} > 240$ kW. The maximum guaranteed RMS current in the power switch is 2 A.

In a boost converter the RMS current through the internal MOSFET depends on both the input and output voltages, according to equations 8a (DCM) and 8b (CCM).



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The current limitation works by clamping the COMP pin voltage proportionally to R_{BILIM}. Peak inductor current is limited to the above threshold decreased by the slope compensation contribution.

Equation 8 a

$$I_{MOS,rms} = \frac{V_{IN} \cdot D}{F_{SW} \cdot L} \sqrt{\frac{D}{3}}$$

Equation 8 b

$$I_{MOS,rms} = I_{OUT} \sqrt{\left(\frac{D}{(1-D)^2} + \frac{1}{12} \left(\frac{V_{OUT}}{I_{OUT} \cdot f_{SW} \cdot L}\right)^2 (D(1-D))^3\right)}$$

5.1.8 Thermal protection

In order to avoid damage due to high junction temperature, a thermal shutdown protection is implemented. When the junction temperature rises above 150 $^{\circ}$ C (typ.), the device turns off both the control logic and the boost converter and holds the FAULT pin low. The LDO is kept alive and normal operation is automatically resumed after the junction temperature has been reduced by 30 $^{\circ}$ C.



5.2 **Backlight driver section**

5.2.1 **Current generators**

The LED7707 is a LEDs driver with six channels (rows); each row is able to drive multiple LEDs in series (max. 36 V) and to sink up to 85 mA maximum current, allowing to manage different kinds of LEDs.

The LEDs current can be set by connecting an external resistor (R_{RILIM}) between the RILIM pin and ground. The voltage across the RILIM pin is internally set to 1.23 V and the rows current is proportional to the RILIM current according to the following equation:

Equation 9

$$I_{ROWx} = \frac{K_R}{R_{RIIIM}}$$

Where $K_R = 1850 \text{ V}$.

The graph in Figure 12 better shows the relationship between I_{ROW} and R_{RII IM} and helps to choose the correct value of the resistor to set the desired row current.

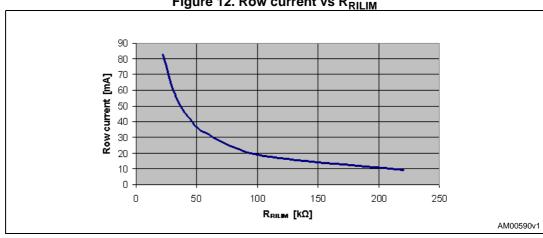


Figure 12. Row current vs RRILIM

The maximum current mismatch between the rows is $\pm 2 \%$ @ $I_{rowx} = 60$ mA.

The LED7707 allows parallelism different rows if required by the application. If the maximum current provided by a single row (85 mA) is not enough for the load, two or more current generators can be connected together, as shown in Figure 13. To keep the parallelism generators stable, the row current should be higher than 10 mA. The connection between channels in parallel must be done as close as possible to the device in order to minimize parasitic inductance.

Operation description LED7707

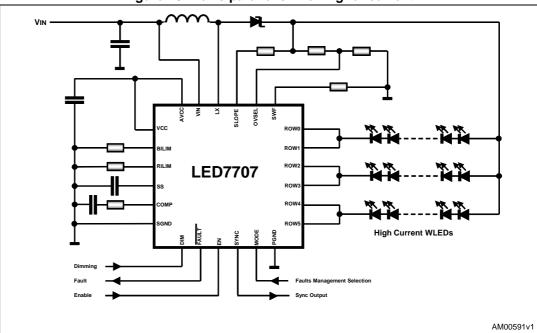


Figure 13. Rows parallelism for higher current



5.2.2 PWM dimming

The brightness control of the LEDs is performed by a pulse-width modulation of the rows current. When a PWM signal is applied to the DIM pin, the current generators are turned on and off mirroring the DIM pin behavior. Actually, the minimum dimming duty-cycle depends on the dimming frequency.

The PWM dimming ratio is limited by the minimum conduction time of the current generators in closed loop operation. A 10 μ s minimum on-time is suggested for proper device operations assuming $I_{ROWs} = 20$ mA, otherwise higher dimming ratio may be required.

Thus, the minimum dimming duty-cycle depends on the dimming frequency according to the following formula:

Equation 10

$$D_{DIM min} = 10 \mu s \cdot f_{DIM}$$

For example, at a dimming frequency of 1 kHz, 1% of dimming duty-cycle can be managed.

During the off-phase of the PWM signal the boost converter is paused and the current generators are turned off. The output voltage can be considered almost constant because of the relatively slow discharge of the output capacitor. During the start-up sequence (see Section 5.1.3 on page 15) the dimming duty-cycle is forced to 100% to detect floating rows regardless of the applied dimming signal.

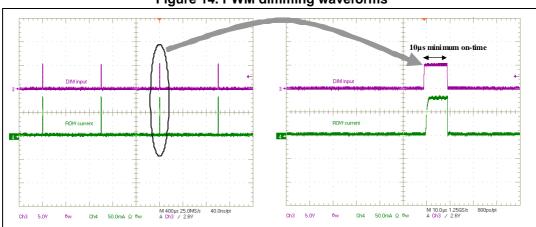


Figure 14. PWM dimming waveforms

5.3 Fault management

The main loop keeps the row having the lowest voltage drop regulated to about 700 mV. This value slightly depends on the voltage across the remaining active rows. After the soft-start sequence, all protections turn active and the voltage across the active current generators is monitored to detect shorted LEDs.

5.3.1 FAULT pin

The FAULT pin is an open-collector output, (with 4 mA current capability) active low, which gives information regarding faulty conditions eventually detected. This pin can be used either to drive a status LED or to warn the host system.



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The FAULT pin status is strictly related to the MODE pin setting (see *Table 5* for details).

5.3.2 MODE pin

The MODE pin is a digital input and can be connected to AVCC or SGND in order to choose the desired fault detection and management. The LED7707 can manage a faulty condition in two different ways, according to the application needs. *Table 5* summarizes how the device detects and handles the internal protections related to the boost section (overcurrent, overtemperature and overvoltage) and to the current generators section (open and shorted LEDs).

FAULT	MODE to GND	MODE to VCC		
Internal MOSFET over-current	FAULT pin HIGH Power MOS turned OFF			
Output over-voltage	FAULT pin LOW Device turned OFF, latched condition			
Thermal shutdown	FAULT pin LOW. device turned OFF. Automatic restart after 30 C temperature drop.			
LED short circuit	FAULT pin LOW, device turned OFF (100s masking time), latched condition (Vth = 4.0 V)	-		
Open row(s)	FAULT pin LOW Device turned OFF at first occurrence, latched condition	FAULT pin HIGH faulty row(s) disconnected.		

Table 6. Faults management summary

5.3.3 Open LED fault

In case a row is not connected or a LED fails open, the device has two different behaviors according to the MODE pin status. If the MODE pin is high (i.e. connected to AVCC), the FAULT pin is set high as soon as the device recognizes the event; the open row is excluded from the control loop and the device continues to work properly with the remaining rows. Thus, if less than six rows are used in the application, the MODE pin must be set high.

Connecting the MODE pin to SGND, the LED7707 behaves in a different manner: as soon as an open row is detected the FAULT pin is tied low and the device is turned off. The internal logic latches this status: to restore the normal operation, the device must be restarted by toggling the EN pin or performing a power-on reset (POR occurs when the voltage at the LDO5 pin falls below the lower UVLO threshold and subsequently rises above the upper one).

Figure 15 shows an example of open channel detection in case of MODE connected to AVCC.

At the point marked as "1" in *Figure 15*, the row opens (row current drops to zero). From this point on the output voltage is increased as long as the output voltage reaches the floating row detection threshold (see *Section 5.1.3 on page 15*). Then (point marked as "2") the faulty row is disconnected and the device keeps on working only with the remaining rows.



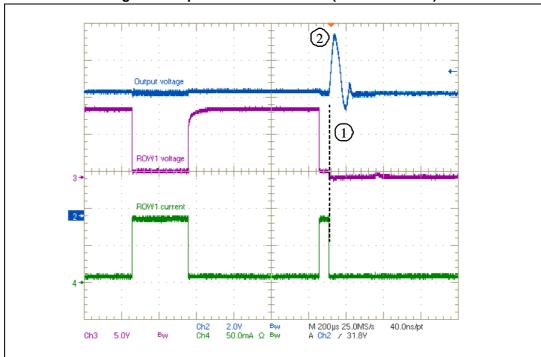


Figure 15. Open channel detection (MODE to AVCC)

5.3.4 Shorted LED fault

When a LED is shorted, the voltage across the related current generator increases of an amount equal to the missing voltage drop of the faulty LED. Since the feedback voltage on each active generator is constantly compared with a fault threshold $V_{TH,FAULT}$, the device detects the faulty condition and acts according to the MODE pin status.

A 100 μ s masking time is introduced to support ESD capacitors eventually connected across the LEDs strings.

If the MODE pin is low, the fault threshold is $V_{TH,FAULT} = 4.0 \text{ V}$. When the voltage across a row is higher than this threshold for more than 100 ms, the FAULT pin is set low and the device is turned off. The internal logic latches this status until the EN pin is toggled or a POR is performed.

In case the MODE pin is connected to AVCC, the LED short-circuit protection is disabled. The LED7707 simply keeps on regulating the set current without affecting the FAULT pin. Despite the higher power dissipation, this option is useful to avoid undesired triggering of the shorted-LED protection simply due to the high voltage drop spread across the LEDs.

Figure 16 shows an example of shorted LED detection in case MODE is connected to GND.

At the point marked as "1" in *Figure 16* one LED fails becoming a short-circuit. The voltage across the current generator of the channel where the failed LED is connected increases by an amount equal to the forward voltage of the faulty LED. Since the voltage across the current generator is above the threshold (4 V), the device is turned off and the fault pin is set low (point "2"). Note that, once a new dimming cycle starts (point "3"), the device waits the masking time (approximately 100 ms) and then sets the FAULT pin low and turns off.



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Operation description LED7707

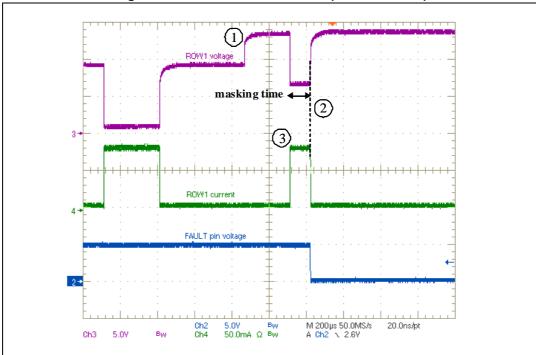


Figure 16. Shorted LED detection (MODE to GND)



6 Application information

6.1 System stability

The boost section of the LED7707 is a fixed frequency, current-mode converter. During normal operation, a minimum voltage selection circuit compares all the voltage drops across the active current generators and provides the minimum one to the error amplifier. The output voltage of the error amplifier determines the inductor peak current in order to keep its inverting input equal to the reference voltage (700 mV typ). The compensation network consists of a simple RC series (R_{COMP} - C_{COMP}) between the COMP pin and ground.

The calculation of R_{COMP} and C_{COMP} is fundamental to achieve optimal loop stability and dynamic performance of the boost converter and is strictly related to the operating conditions.

6.1.1 Loop compensation

The compensation network can be quickly calculated using equations 11 to 16. Once both R_{COMP} and C_{COMP} have been determined, a fine-tuning phase may be required in order to get the optimal dynamic performance from the application.

The first parameter to be fixed is the switching frequency. Normally, a high switching frequency allows reducing the size of the inductor and positively affects the dynamic response of the converter (wider bandwidth) but increases the switching losses. For most of applications, the fixed value (660 kHz) represents a good trade-off between power dissipation and dynamic response, allowing to save an external resistor at the same time. In low-profile applications, the inductor value is often kept low to reduce the number of turns; an inductor value in the $4.7 \,\mu\text{H}-15 \,\mu\text{H}$ range is a good starting choice.

In order to avoid instability due to interaction between the DC-DC converter's loop and the current generators' loop, the bandwidth of the boost should not exceed the bandwidth of the current generators. A unity-gain frequency (f_U) in the order of 30-40 kHz is acceptable. Also, take care not to exceed the CCM-mode right half-plane zero (RHPZ).

Equation 11

$$f_U \le 0.2 \cdot F_{SW}$$

Equation 12

$$f_U \leq 0.2 \cdot \frac{M^2 R}{2\pi \cdot L} = 0.2 \cdot \frac{\left(\frac{V_{IN,min}}{V_{OUT}}\right)^2 \left(\frac{V_{OUT}}{I_{OUT}}\right)}{2\pi \cdot L}$$

Equation 13a

$$M = \frac{V_{IN,min}}{V_{OUT}}$$



Equation 14b

$$R = \frac{V_{OUT}}{I_{OUT}}$$

Where $V_{IN,min}$ is the minimum input voltage and I_{OUT} is the overall output current.

Note that, the lower the inductor value (and the higher the switching frequency), the higher the bandwidth can be achieved. The output capacitor is directly involved in the loop of the boost converter and must be large enough to avoid excessive output voltage drop in case of a sudden line transition from the maximum to the minimum input voltages.

However a more significant requirement concerns the output voltage ripple.

The output capacitor should be chosen in accordance with the following expression:

Equation 15

$$C_{OUT} > \frac{\left(I_{L,peak} - I_{OUT}\right) \cdot T_{OFF}}{2 \cdot \Delta V_{OUT max}}$$

where $\Delta V_{OUT, max}$ is the maximum acceptable output voltage ripple, $I_{L, peak}$ is the peak inductor current, T_{OFF} is the off-time of the switching cycle (for an extensive explanation see Section 6.4.4 on page 34).

Once the output capacitor has been chosen, the R_{COMP} can be calculated as:

Equation 16

$$R_{COMP} = \frac{2\pi \cdot f_U \cdot C}{G_M \cdot g_{FA} \cdot M}$$

Where GM = 2.7 S and g_{EA} = 375 μ s

Equation 15 places the loop bandwidth at f_U . Then, the C_{COMP} capacitor is determined to place the frequency of the compensation zero 5 times lower than the loop bandwidth:

Equation 17

$$C_{COMP} = \frac{1}{2\pi \cdot f_Z \cdot R_{COMP}}$$

Where $f_7 = f_U/5$.

In most of the applications an experimental approach is also very valid to compensate the circuit. A simple technique to optimize different applications is to choose $C_{COMP}=4.7~nF$ and to replace R_{COMP} with a 10 k Ω trimmer adjusting its value to properly damp the output transient response. Insufficient damping will result in excessive ringing at the output and poor phase margin.

Figure 17 (a and b) give an example of compensation adjustment for a typical application.

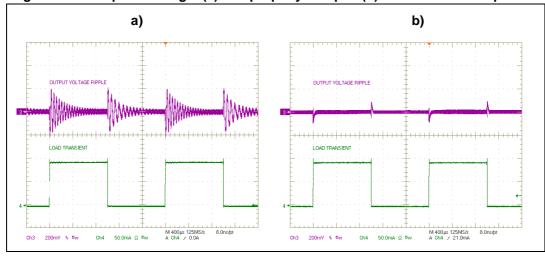
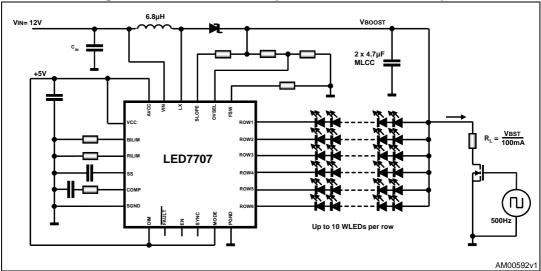


Figure 17. Poor phase margin (a) and properly damped (b) load transient responses





6.2 Thermal considerations

In order to prevent the device from exceeding the thermal shutdown threshold (150 °C), it is important to estimate the junction temperature through the following equation:

Equation 18

$$T_J = T_A + R_{th.JA} \cdot P_{D.tot}$$

where T_A is the ambient temperature, $R_{th,JA}$ is the equivalent thermal resistance junction to ambient and $P_{D,tot}$ is the power dissipated by the device.

The $R_{th,JA}$ measured on the application demonstration board (described in Section 6.5) is 42 °C/W.

The P_{D.tot} has several contributions, listed below.



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Conduction losses due to the R_{DS(on)} of the internal power switch, equal to:

Equation 19

$$P_{D.cond} = R_{DSon} \cdot I_{IN}^2 \cdot D \cdot D_{DIM}$$

where D is defined as:

Equation 20

$$D = 1 - \frac{V_{IN}}{V_{OUT}}$$

and $\ensuremath{D_{\text{DIM}}}$ is the duty cycle of the PWM dimming signal.

Switching losses due to the power MOSFET turn on and off, calculated as:

Equation 21

$$P_{D,sw} = V_{OUT} \cdot I_{IN} \cdot f_{sw} \cdot \frac{(t_r + t_f)}{2} \cdot D_{DIM}$$

where t_r and t_f are the power MOSFET rise time and fall time respectively.

Current generators losses. This contribution is strictly related to the LEDs used in the application. Only the contribution of the leading current generator ("master" current generator) can be predicted, regardless of the LEDs forward voltage:

Equation 22

$$P_{GEN,Master} = I_{ROW} \cdot V_{IFB} \cdot D_{DIM}$$

where I_{ROW} is the current flowing through the row, whereas V_{IFB} is the voltage across the master current generator (typically 700 mV).

The voltages across the other current generators depend on the spread of the LEDs forward voltage. The worst case for power dissipation (maximum forward voltage LEDs in the master row, minimum forward voltage LEDs in all other rows) can be estimated as:

Equation 23

$$P_{GEN} = I_{ROW} \cdot \left(n_{ROWs} - 1 \right) \cdot \left(V_{IFB} + \Delta V_{f, LEDs} \cdot n_{LEDs} \right) \cdot D_{DIM}$$

where n_{ROWs} is the number of active rows, $\Delta V_{f,LEDs}$ is the spread of the LEDs forward voltage and n_{LEDs} is the number of LEDs per row.

LDO losses, due to the dissipation of the 5 V linear regulator:

Equation 24

$$P_{D,LDO} = (V_{IN} - V_{LDO}) \cdot I_{LDO}$$

The LED7707 is housed in a 24 leads 4x4-VFQFPN package with exposed pad that allows good thermal performance. However it is also important to design properly the demonstration board layout in order to assure correct heat dissipation.



Figure 19 shows a picture of the LED7707 application demonstration board taken using an infrared camera. The chip temperature, in those application conditions, is kept below 50 °C.

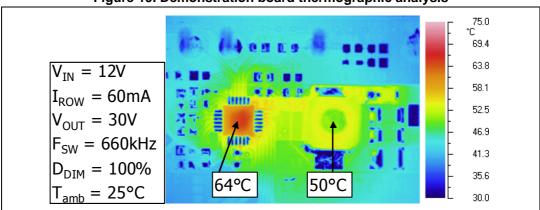


Figure 19. Demonstration board thermographic analysis

6.3 Component selection

6.3.1 Inductor selection

Being the LED7707 mostly dedicated to backlighting, real-estate applications dictate severe constrain in selecting the optimal inductor. The inductor choice must take into account different parameters like conduction losses (DCR), core losses (ferrite or iron-powder), saturation current and magnetic-flux shielding (core shape and technology).

The switching frequency of the LED7707 can be set in the 200 kHz-1 MHz range, allowing a wide selecting room for the inductance value. Low switching frequencies takes to high inductance value, resulting in significant DCR and size. On the other hand, high switching frequencies result in significant core losses. The suggested range is 4.7-22 μ H, even if the best trade off between the different loss contributions varies from manufacturer to manufacturer.

A 6.8 µH inductor has been experimentally found as the most suitable for applications running at a 660 kHz switching frequency.

Manufacturer	Part number	Description	Size
Coilcraft	LPS6235-682MLC	$6.8~\mu H$, $75~m\Omega$, $2.7~A$	6x6 mm
Coilcraft	XPL7030-682ML	$6.8~\mu H$, $60~m\Omega$, $5.8~A$	7x7 mm
Wurth	7440650068	$6.8~\mu\text{H},33~\text{m}\Omega,3.6~\text{A}$	10x10 mm

Table 7. Recommended inductors

6.3.2 Capacitors selection

The input and output capacitors should have very low ESR (ceramic capacitors) in order to minimize the ripple voltage. The boost converter of the LED7707 has been designed to support ceramic capacitors. The required capacitance depends on the programmed LED current and the minimum dimming frequency (the boost converter is off when the DIM pin is



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low and the output capacitor is slowly discharged). Considering the worst case (i.e. 200 Hz dimming frequency and 85 mA/channel), two 4.4 μF MLCCs are suitable for almost all applications. Particular care must be taken when selecting the rated voltage and the dielectric type of the output capacitors: 50 V rated MLCC may show a significant capacitance drop when biased, especially in case of Y5V dielectric.

As in most of boost converters, the input capacitor is less critical, although it is necessary to reduce the switching noise on the supply rail. The input capacitor is also important for the internal LDO of the LED7707 and must be kept as close as possible to the chip. The rated voltage of the input capacitor can be chosen according to the supply voltage range; a 10 μ F X5R MLCC is recommended.

 Manufacturer
 Part number
 Description
 Package
 Notes

 Taiyo Yuden
 UMK325BJ106KM-T
 Ceramic, 35V, X5R, 20%
 SMD 1210
 C_{IN}

 Murata
 GRM31CR71H225KA88B
 Ceramic, 50V, X7R, 20%
 SMD 1206
 C_{OUT}

Table 8. Recommended capacitors

6.3.3 Flywheel diode selection

The flywheel diode must be a Schottky type to minimize the losses. This component is subject to an average current equal to the output one and must sustain a reverse voltage equal to the maximum output rail voltage. Considering all the channels sinking 75 mA each (i.e. 450 mA output current) and the maximum output voltage (36 V), the STP1L40M ($I_{f,ave} = 1 \text{ A}, V_r = 40 \text{ V}$) diode is a good choice. Smaller diodes can be used in applications involving lower output voltage and/or lower output current.

6.4 Design example

In order to help the design of an application using the LED7707, in this section a simple step-by-step design example is provided.

A possible application could be the LED backlight in a 17" LCD panel using the LED7707.

Here below the possible application conditions are listed:

- $V_{IN} = 12 \pm 10\%$
- 4 strings of 42 white LEDs (60 mA) each (arranged in 6 rows, 7LEDs per row)
- V_{F. LEDs} = 3.5 V ± 200 mV

6.4.1 Switching frequency setting

To reduce the number of the external components, the default switching frequency is selected (660 kHz typ.) by connecting the FSW pin to AVCC pin.

However, in case a different switching frequency is required, a resistor from FSW pin and ground can be connected, according to the equation (5).

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6.4.2 Row current setting

Considering the equation 9 in Section 5.2.1, the R_{RILIM} resistor can be calculated as:

Equation 25

$$R_{RILIM} = \frac{K_R}{I_{ROW}} = \frac{1850 \text{ V}}{60 \text{ mA}} = 30.83 \text{k}\Omega$$

The closest standard commercial value is 30 k Ω . The actual value of the row current will be a little lower (61.7 mA).

6.4.3 Inductor choice

The boost section, as all DC-DC converters, can work in CCM (continuous conduction mode) or in DCM (discontinuous conduction mode) depending on load current, input and output voltage and other parameters, among which the inductor value.

In a boost converter it is usually preferable to work in DCM.

Once the load, the input and output voltage, and the switching frequency are fixed, the inductor value defining the boundary between DCM and CCM operation can be calculated as:

Equation 26

$$L_{B} = \frac{R_{0} \cdot D \cdot (1 - D)^{2}}{2 \cdot F_{SW}}$$

where D is the duty-cycle defined as:

Equation 27

$$D = 1 - \frac{V_{IN}}{V_{OUT}} = \begin{cases} 0.59 & @ & V_{IN,min} = 10.8V \\ 0.50 & @ & V_{IN,max} = 13.2V \end{cases}$$

where as R₀ is:

Equation 28

$$R_0 = \frac{V_{OUT}}{I_{OUT}} = 74\Omega$$

and

Equation 29

$$I_{OUT} = 6 \cdot I_{ROW} = 360 \text{mA}$$

The output voltage in the above calculations is considered as the maximum value (LED with the maximum forward voltage connected to the leading generator):



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Equation 30

$$V_{OUT.max} = 7 \cdot V_{F.LEDs.max} + 700 \text{mV} = 26.6 \text{V}$$

Considering the input voltage range, the lower L_{B} will be at the lower input voltage. Hence the condition to assure the DCM operation becomes:

Equation 31

$$L < L_B(V_{IN min}) = 5.6 \mu H$$

An inductor value of 4.7 μH could be a suitable value, considering also a margin from the boundary condition.

It is important to highlight that the inductor choice involves not only the value itself but the saturation current (higher than the current limit, see <u>Section 6.4.4</u>), the rated RMS current (the compliance with the saturation current might be not enough; also the thermal performances must be taken into account), the DCR (which affects the efficiency) and the size (in some application might be a strict requirement).

However the DCR can't be reduced keeping the size small. Hence a trade off between these two requirements must be achieved according to the application.

6.4.4 Output capacitor choice

The choice of the output capacitor is mainly affected by the desired output voltage ripple.

Since the voltage across the LEDs can be considered almost constant, this ripple is transferred across the current generators, affecting their dynamic response.

The output ripple can be estimated as (neglecting the contribution of ESR of C_{OUT} , very low in case of MLCC):

Equation 32

$$\Delta V_{OUT} = \frac{\left(I_{L,peak} - I_{OUT}\right) \cdot T_{OFF}}{2 \cdot C_{OUT}}$$

where I_{L. peak} is the inductor peak current (see Figure 20) calculated as:

Equation 33

$$I_{L,peak} = \frac{V_{IN} \cdot D}{F_{sw} \cdot L} = \begin{cases} 1.915 A & @ & V_{IN,min} = 10.8 V \\ 1.762 A & @ & V_{IN,max} = 13.2 V \end{cases}$$

whereas D, working in DCM, is:

Equation 34

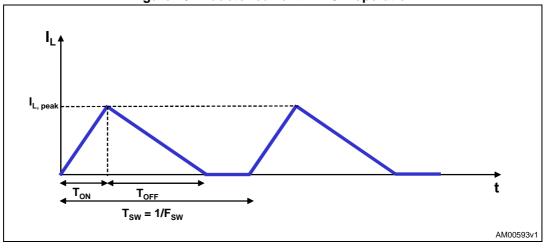
$$D = \sqrt{\frac{2 \cdot F_{sw} \cdot L \cdot M(M-1)}{R_0}} = \begin{cases} 0.55 & @ V_{IN,min} = 10.8V \\ 0.414 & @ V_{IN,max} = 13.2V \end{cases}$$

defining M as:

Equation 35

$$M = \frac{V_{OUT}}{V_{IN}} \begin{cases} 2.463 & @ V_{IN,min} = 10.8V \\ 2.015 & @ V_{IN,max} = 13.2V \end{cases}$$

Figure 20. Inductor current in DCM operation



T_{OFF} can be calculated as:

Equation 36

$$T_{OFF} = T_{SW} \cdot D_2 = \begin{cases} 569.7 \text{ns} & @ V_{IN,min} = 10.8 \text{V} \\ 618.2 \text{ns} & @ V_{IN,max} = 13.2 \text{V} \end{cases}$$

defining D₂ as:

Equation 37

$$D_2 = \sqrt{\frac{2 \cdot F_{SW} \cdot L \cdot M}{R_0 \cdot (M-1)}} = \begin{cases} 0.376 & @ & V_{IN,min} = 10.8V \\ 0.408 & @ & V_{IN,max} = 13.2V \end{cases}$$

The worst case for the output voltage ripple is when input voltage is lower (V_{IN.min} = 10.8 V).

A simple way to select the C_{OUT} value is fixing a maximum voltage ripple.

In order to affect as less as possible the current generators, it would be better to fix the maximum ripple lower than the typical voltage across the generators.

For example considering ΔV_{OUT} lower than 70 mV (i.e. the 10% of the voltage across the leading generator), the required capacitance is:

Equation 38

$$C_{OUT} > \frac{\left(I_{L,peak} - I_{OUT}\right) \cdot T_{OFF}}{2 \cdot \Delta V_{OUT,max}} = 6.33 \mu F$$

A margin from the calculated value should be taken into account because of the capacitance drop due to the applied voltage when MLCCs are used.



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One 10 µF MLCC (or two 4.7 µF MLCCs) can be a good choice for this application.

In case a dimming duty cycle different from 100% is used, a further contribution to the capacitor discharge (during the off time of the dimming cycle) should be considered.

6.4.5 Input capacitor choice

The input capacitor of a boost converter is less critical than the output capacitor, due to the fact that the inductor is in series with the input, and hence, the input current waveform is continuous.

A low ESR capacitor is always recommended.

A capacitor of 10 µF is tentatively a good choice for most of the applications.

6.4.6 Overvoltage protection divider setting

The over-voltage protection (OVP) divider provides a partition of the output voltage to the OVSEL pin. The OVP divider setting not only fixes the OVP threshold, but also the open-channel detection threshold.

The proper OVP divider setting can be calculated by the equation (3):

Equation 39

$$R_2 = R_1 \cdot \frac{1.145V}{V_{OUT,MAX} + 4V - 1.145V}$$

where $V_{OUT, MAX}$ is the maximum output voltage considering the worst case (all LEDs with the maximum $V_F = V_{F,max} = 3.7 \text{ V}$ on the same row):

Equation 40

$$V_{OUT\ OVP} = nLED \cdot V_{F\ max} + 700mV = 26.6V$$

 R_1 can be chosen is in the order of hundreds of kilo-ohms to reduce the leakage current in the resistor divider. For example, setting R_1 = 510 k Ω leads to R_2 = 21.89 k Ω . The closest standard commercial value is R_2 = 22 k Ω .

6.4.7 Compensation network

For the compensation network, the suggestions provided in Section 6.1 are always valid.

In this condition, tentatively the following value of R3 and C8 (see *Figure 23*) are usually a good choice for the loop stability:

 $R3 = 2.4 \text{ k}\Omega$

C8 = 4.7 nF

6.4.8 Boost current limit

The boost current limit is set to protect the internal power switch against excessive current. The slope compensation may reduce the programmed current limit. Hence, to take into account this effect, as a rule of thumb, the current limit can be set as twice as much the maximum inductor peak current (see Section 6.4.4):



I_{BOOST, PEAK} > 3.83 A

Therefore, using equation (7) and choosing $I_{BOOST, PEAK} = 4 A$, R_{BILIM} is:

Equation 41

$$R_{BILIM} = \frac{K_B}{I_{BOOSTPEAK}} = 300k\Omega$$

6.4.9 Power dissipation estimate

As explained in section 5.2, there are several contributions to the total power dissipation.

Neglecting the power dissipated by the LDO (surely less significant compared with the other contributions), equation (18), (20), (21) and (22) help to estimate the overall power dissipation.

Before starting the power dissipation estimate it is important to highlight that the following calculations are considering the worst case (the actual value of the dissipated power would require measurements). Therefore the power dissipation is estimated according to the following assumptions:

- 1. Minimum input voltage (10.8 V), which leads to maximum input current (and also D will have the higher value, see Section 6.4.4)
- 2. Maximum R_{DS(on)} of the internal power MOSFET
- 3. LEDs in the row of the leading generator will have the maximum forward voltage, whereas all other LEDs in the other rows will have the minimum forward voltage
- 4. 100% dimming signal duty cycle is considered

The conduction and switching losses on the internal power switch can be calculated as:

Equation 42

$$P_{D,cond} = R_{DSon} \cdot I_{IN}^2 \cdot D \cdot D_{DIM} = 216 \text{mW}$$

Equation 43

$$P_{D,sw} = V_{OUT} \cdot I_{IN} \cdot f_{sw} \cdot \frac{(t_r + t_f)}{2} \cdot D_{DIM} = 233 \text{mW}$$

where $t_r = t_f = 15 \text{ ns}$

The power dissipation related to the current generators is given by:

Equation 44

$$P_{GEN\,Master} = I_{ROW} \cdot V_{IEB} \cdot D_{DIM} = 42mW$$

Equation 45

$$P_{GEN} = I_{ROW} \cdot \left(n_{ROWs} - 1 \right) \cdot \left(V_{IFB} + \Delta V_{f, LEDs} \cdot n_{LEDs} \right) \cdot D_{DIM} = 630 \text{mW}$$



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Equation 46

$$P_{D.tot} \cong P_{D.cond} + P_{D.sw} + P_{GEN.Master} + P_{GEN} = 1.12W$$

The junction temperature can be estimated by equation (18) considering $T_A = 25$ °C:

Equation 47

$$T_J = T_{Amb} + R_{th,JA} \cdot P_{D,tot} = 72^{\circ}C$$

In order to estimate also the efficiency, other contributions to the power dissipation must be added to $P_{D. tot}$ (which represents only the power dissipated by the device), that is:

Equation 48

$$P_{DISS,Diode} = V_{F,Diode} \cdot I_{IN} \cdot D_2 = 133mW$$

where $V_{F, Diode} = 0.4 V$

Equation 49

$$P_{DISS, Ind} = DCR \cdot I_{Ind, RMS}^2 \cong DCR \cdot I_{IN}^2 = 63mW$$

where DCR = 80 m Ω (typical DCR of the recommended inductors).

Therefore the total dissipated power is:

Equation 50

$$P_{DISS,TOTAL} = P_{D,tot} + P_{DISS,Diode} + P_{DISS,Ind} = 1.316W$$

Considering the input power as the result of input voltage multiplied by the input current, the estimated efficiency is:

Equation 51

$$\eta = \frac{P_{IN} - P_{DISS,TOT}}{P_{IN}} = 0.862$$

Note:

It is important to remind that the previous calculations consider the worst case, especially for the power dissipated on the current generators.

Statistical analysis (confirmed by bench measurements) shows that the series connection of more LEDs on each channel leads to compensation effects.

The hypothesis 3 above mentioned is thus rather unlikely.

Therefore P_{GEN} is significantly lower and the overall efficiency is typically around 90%.

6.5 Layout consideration

- 1. A careful PCB layout is important for proper operation. In this section some guidelines are provided in order to achieve a good layout.
- The device has two different ground pins: signal ground (SGND) and power ground (PGND). The PGND pin handles the switching current related to the boost section; for this reason the PCB traces should be kept as short as possible and with adequate width.
- 3. The signal ground is the return for the device supply and the current generators and can be connected to the thermal pad.
- 4. The heat dissipation area (adequate to the application conditions) should be placed backside respect to the device and with the lowest thermal impedance possible (i.e. PCB traces in the backside should be avoided). The dissipation area is thermally and electrically connected to the thermal pad by several vias (nine vias are recommended).
- 5. The signal and power grounds must be connected together in a single point as close as possible to the PGND pin to reduce ground loops.
- The R-C components of the compensation network should be placed as close as possible to the COMP pin in order to avoid noise issue and instability of the compensation.
- Noise sensitive signals (i.e. feedbacks and compensation) should be routed as short as
 possible to minimize noise collection. The LED7707 pinout makes it easy to separate
 power components (e.g. inductor, diode) from signal ones.
- 8. The LX switching node should have and adequate width for high efficiency.
- 9. The critical power path inductor-LX-PGND must be as short as possible by mounting the inductor, the diode and COUT as close as possible each other.
- 10. The capacitors of the compensated divider connected to the OVSEL pin should be placed as close as possible to the OVSEL pin.
- 11. In order to assure good performance in terms of row current accuracy/mismatch, the PCB traces from the rows pins to the LEDs should have similar length and width.
- 12. The capacitors of the filter connected to LDO5 and VIN pins should be mounted as close as possible to the mentioned pins.

Figure 21 and Figure 22 shows the demonstration board layout (top view and bottom view respectively).



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SW3 R5 C9 C10 C13 D3 C12

FSW C4 C4 C4

AVCC R6 R7

FN D2 R11

FAULT R0V1 R0V2 R0V3 R0V4 R0V5 R0V6

VBOOST

VBOOST

VBOOST

VBOOST

Figure 21. Demonstration board layout (top view)

Figure 22. Demonstration board layout (bottom view)

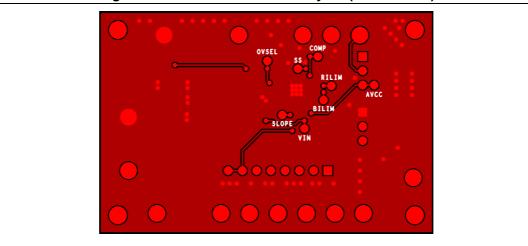


Figure 23 shows the LED7707 demonstration board application circuit, whereas *Table 9* lists the used components and their value.

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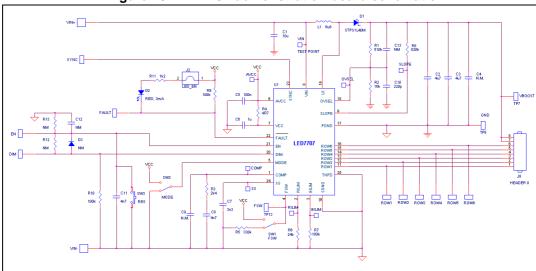


Figure 23. LED7707 demonstration board schematic



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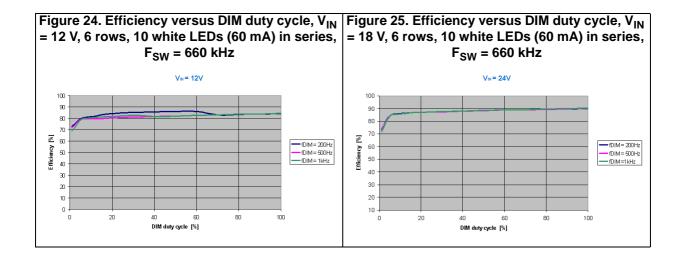
Table 9. LED7707 demonstration board component list

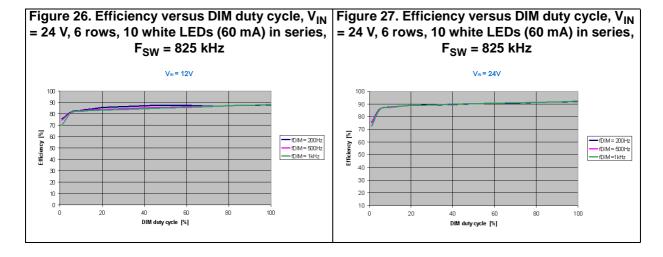
C1 Ceramic, 35 V XSR, 20 % SKD 1210 UMK325BJ106KM-T Taiyo Yuden 10 μF C2, C3 Ceramic, 50 V X7R, 20 % X7R, 20 % SMD 1206 GRM31CR71H475KA88B Murata 4.7 μF C5 X7R, 20 % X7R, 20 % X7R, 20 % X7R, 20 % SMD 1206 GRM31CR71H225KA88B HµF 1 μF C6 C7 SMD 1206 GRM31CR71H225KA88B Murata N.M. C7 C8 Ceramic, 25 V X5R, 20% SMD 0603 Standard 53.3 nF C10 C11 SMD 0603 Standard 15 pF R1 R2 Chip resistor 0.1 W, 1% SMD 0603 Standard 330 kΩ R8 Chip resistor 0.1 W, 1% SMD 0603 Standard 360 kΩ R7 Chip resistor 0.1 W, 1% SMD 0603 Standard 360 kΩ R8 R9, R10 Standard 660 kΩ R1 R1 N.M. N.M. L1 6u8, 60 mΩ, 5.8 A 7x7 mm XPL7030-682ML Coilcraft 6.8 μF D1 Schottky, 40 V, 1 A D0216-AA STPS1L40M ST	Component	Description	Package	Part number	MFR	Value
C4 X7R, 20 % SMD 1206 GRM31CR71H225KA88B Murata N.M. C5 C6 1 μF 100 nF 3.3 nF 1.4 nF 100 nF 3.3 nF 4.7 nF N.M. 220 pF 4.7 nF N.M. 220 pF 4.7 nF N.M. 15 pF N.M. 15 pF N.M. 15 pF N.M. 16 kΩ 2.4 kΩ 4.7 Ω 330 kΩ 2.4 kΩ 100 kΩ 100 kΩ 100 kΩ 1.2 kΩ N.M.	C1		SMD 1210	UMK325BJ106KM-T	Taiyo Yuden	10 μF
C4 A7R, 20% SMD 1206 GRM31CR71H225KA88B N.M. C5 C6 1 μF 100 nF C7 3.3 nF 4.7 nF C8 M.M. 220 pF C10 4.7 nF N.M. C11 15 pF 4.7 nF R1 N.M. 15 pF R1 F10 kΩ 16 kΩ R2 A7 Ω 330 kΩ R4 A7 Ω 330 kΩ R6 24 kΩ R7 Chip resistor 0.1 W, 1% SMD 0603 Standard R8 89, R10 Standard 360 kΩ R8 89, R10 R1 1.2 kΩ R11 L1 6u8, 60 mΩ, 5.8 A 7x7 mm XPL7030-682ML Coilcraft 6.8 μF R13 L1 5chottky, 40 V, 1 A DO216-AA STPS1L40M ST STPS1L40M D2 Red LED, 3 mA SMD 0603 Standard BAS69 N.M. D3 Signal Schottky SOD-523 BAS69 N	C2, C3	Ceramic, 50 V	SMD 1206	GRM31CR71H475KA88B		4.7 μF
C6 C7 100 nF C7 C8 4.7 nF C9 X5R, 20% SMD 0603 C10 10 M.M. C11 220 pF C11 4.7 nF N.M. 15 pF R1 R2 R3 Chip resistor 0.1 W, 1% R6 510 kΩ R7 Chip resistor 0.1 W, 1% R8 SMD 0603 R9, R10 Standard R11 680 kΩ R9, R10 100 kΩ R11 1.2 kΩ R12 N.M. R13 N.M. L1 6u8, 60 mΩ, 5.8 A 7x7 mm XPL7030-682ML Coilcraft 6.8 μF R1 N.M. N.M. N.M. N.M. D2 Red LED, 3 mA SMD 0603 Standard Standard D3 Signal Schottky SOD-523 BAS69 N.M. U1 Integrated circuit QFN4x4 LED7707 ST LED7707 J2 PCB pad jumper PCB pad jumper LED7707 ST LED7707 </td <td>C4</td> <td></td> <td>SMD 1206</td> <td>GRM31CR71H225KA88B</td> <td>Murata</td> <td>N.M.</td>	C4		SMD 1206	GRM31CR71H225KA88B	Murata	N.M.
C7 C8 Ceramic, 25 V X5R, 20% SMD 0603 Standard 1.47 nF 4.7 nF N.M. 220 pF 4.7 nF N.M. 220 pF 4.7 nF N.M. 15 pF N.M. 15 pF N.M. 15 pF N.M. 16 kΩ 2.4 kΩ 4.7 Ω 330 kΩ 2.4 kΩ 2.4 kΩ 4.7 Ω 300 kΩ 2.4 kΩ 2.4 kΩ 2.4 kΩ 2.2 kΩ <	C5					1 μF
C8 Ceramic, 25 V X5R, 20% SMD 0603 Standard N.M. C10 220 pF 4.7 nF C11 220 pF 4.7 nF C12 N.M. 15 pF R1 N.M. 15 pF R2 SMD 0603 Standard 2.4 kΩ R5 R6 2.4 kΩ 4.7 Ω R7 Chip resistor 0.1 W, 1% SMD 0603 Standard 360 kΩ R8 R9, R10 Standard 360 kΩ R11 R12 N.M. N.M. R13 N.M. N.M. L1 6u8, 60 mΩ, 5.8 A 7x7 mm XPL7030-682ML Coilcraft 6.8 μF D1 Schottky, 40 V, 1 A D0216-AA STPS1L40M ST STPS1L40M D2 Red LED, 3 mA SMD 0603 Standard Standard D3 Signal Schottky SOD-523 BAS69 N.M. U1 Integrated circuit QFN4x4 LED7707 ST LED7707 J8 Header 8	C6					100 nF
C9 Ceramic, 25 V X5R, 20% SMD 0603 Standard N.M. C10 220 pF 4.7 nF C12 N.M. 15 pF C13 R1 F5 510 kΩ R2 R3 Chip resistor 0.1 W, 1% SMD 0603 Standard 2.4 kΩ R5 R6 24 kΩ 4.7 Ω 330 kΩ R8 R9, R10 SMD 0603 Standard 360 kΩ R11 R12 N.M. 100 kΩ R11 R12 N.M. N.M. R13 L1 6u8, 60 mΩ, 5.8 A 7x7 mm XPL7030-682ML Coilcraft 6.8 μF D1 Schottky, 40 V, 1 A DO216-AA STPS1L40M ST STPS1L40M D2 Red LED, 3 mA SMD 0603 Standard D3 Signal Schottky SOD-523 BAS69 N.M. U1 Integrated circuit QFN4x4 LED7707 ST LED7707 J2 PCB pad jumper Jen Change of the circuit Red Led R SI	C7		SMD 0603			3.3 nF
C10	C8					4.7 nF
C10 C11 220 pF 4.7 nF C12 N.M. 15 pF R1 R2 F510 kΩ 16 kΩ R3 Chip resistor 0.1 W, 1% SMD 0603 Standard 2.4 kΩ R5 24 kΩ R6 24 kΩ R7 Chip resistor 0.1 W, 1% SMD 0603 Standard 360 kΩ R8 R9, R10 T1.2 kΩ 100 kΩ R11 R12 N.M. N.M. R13 N.M. N.M. L1 6u8, 60 mΩ, 5.8 A 7x7 mm XPL7030-682ML Coilcraft 6.8 μF D1 Schottky, 40 V, 1 A DO216-AA STPS1L40M ST STPS1L40M D2 Red LED, 3 mA SMD 0603 Standard D3 Signal Schottky SOD-523 BAS69 N.M. U1 Integrated circuit QFN4x4 LED7707 ST LED7707 J2 PCB pad jumper SIL 8 Standard SW1, SW2 Jumper 3 SIL 8 Standard	C9				Standard	N.M.
C12 C13 N.M. 15 pF R1 FR1 FR2 FS10 kΩ 16 kΩ 2.4 kΩ 16 kΩ 2.4 kΩ 4.7 Ω 330 kΩ 24 kΩ 4.7 Ω 330 kΩ 24 kΩ 24 kΩ 24 kΩ 24 kΩ 24 kΩ 24 kΩ 2.4 kΩ <td< td=""><td>C10</td><td>, AJN, 2076</td><td></td><td></td><td>220 pF</td></td<>	C10	, AJN, 2076				220 pF
C13 R1 15 pF R1 R2 510 kΩ R3 Chip resistor 0.1 W, 1% 2.4 kΩ R5 24 kΩ R6 24 kΩ R7 Chip resistor 0.1 W, 1% SMD 0603 Standard 360 kΩ R8 R9, R10 100 kΩ 100 kΩ R11 R12 N.M. N.M. R13 N.M. N.M. L1 6u8, 60 mΩ, 5.8 A 7x7 mm XPL7030-682ML Coilcraft 6.8 μF D1 Schottky, 40 V, 1 A D0216-AA STPS1L40M ST STPS1L40M D2 Red LED, 3 mA SMD 0603 Standard D3 Signal Schottky SOD-523 BAS69 N.M. U1 Integrated circuit QFN4x4 LED7707 ST LED7707 J2 PCB pad jumper LED7707 ST LED7707 J8 Header 8 SIL 8 Standard SW1, SW2 Jumper 3 SIL 3 Standard	C11					4.7 nF
R1 R2 Standard 16 kΩ R3 Chip resistor 0.1 W, 1% SMD 0603 Standard 2.4 kΩ R5 Chip resistor 0.1 W, 1% SMD 0603 Standard 360 kΩ R8 R9, R10 SMD 0603 Standard 100 kΩ R11 R12 N.M. R13 N.M. N.M. L1 6u8, 60 mΩ, 5.8 A 7x7 mm XPL7030-682ML Coilcraft 6.8 μF D1 Schottky, 40 V, 1 A D0216-AA STPS1L40M ST STPS1L40M D2 Red LED, 3 mA SMD 0603 Standard D3 Signal Schottky SOD-523 BAS69 N.M. U1 Integrated circuit QFN4x4 LED7707 ST LED7707 J2 PCB pad jumper J8 Header 8 SIL 8 Standard SW1, SW2 Jumper 3 SIL 3 Standard	C12					N.M.
R2 R3 Chip resistor 0.1 W, 1% SMD 0603 Standard 2.4 kΩ R5 Chip resistor 0.1 W, 1% SMD 0603 Standard 360 kΩ R8 A Standard 360 kΩ 100 kΩ R9, R10 R11 1.2 kΩ R12 N.M. R13 N.M. D1 Schottky, 40 V, 1 A DO216-AA STPS1L40M ST STPS1L40M D2 Red LED, 3 mA SMD 0603 Standard D3 Signal Schottky SOD-523 BAS69 N.M. U1 Integrated circuit QFN4x4 LED7707 ST LED7707 J2 PCB pad jumper Jamper 3 SIL 8 Standard SW1, SW2 Jumper 3 SIL 3 Standard	C13					15 pF
R3 Chip resistor 0.1 W, 1% SMD 0603 Standard 2.4 kΩ R5 R6 24 kΩ R7 Chip resistor 0.1 W, 1% SMD 0603 Standard 360 kΩ R8 R9, R10 R11 680 kΩ 100 kΩ R11 R12 N.M. R13 N.M. N.M. D1 Schottky, 40 V, 1 A DO216-AA STPS1L40M ST STPS1L40M D2 Red LED, 3 mA SMD 0603 Standard Standard D3 Signal Schottky SOD-523 BAS69 N.M. U1 Integrated circuit QFN4x4 LED7707 ST LED7707 J2 PCB pad jumper PCB pad jumper SIL 8 Standard SW1, SW2 Jumper 3 SIL 3 Standard	R1		SMD 0603			510 kΩ
R4	R2					16 kΩ
R4 0.1 W, 1% SMD 0603 Standard 4.7 Ω R6 Chip resistor 0.1 W, 1% SMD 0603 Standard 360 kΩ R8 680 kΩ 100 kΩ R11 1.2 kΩ R12 N.M. R13 N.M. L1 6u8, 60 mΩ, 5.8 A 7x7 mm XPL7030-682ML Coilcraft 6.8 μF D1 Schottky, 40 V, 1 A D0216-AA STPS1L40M ST STPS1L40M D2 Red LED, 3 mA SMD 0603 Standard D3 Signal Schottky SOD-523 BAS69 N.M. U1 Integrated circuit QFN4x4 LED7707 ST LED7707 J2 PCB pad jumper FN4x4 LED7707 ST LED7707 J8 Header 8 SIL 8 Standard SW1, SW2 Jumper 3 SIL 3 Standard	R3				Standard -	2.4 kΩ
R6 Chip resistor 0.1 W, 1% SMD 0603 Standard 360 kΩ R8 680 kΩ 100 kΩ 100 kΩ R11 1.2 kΩ N.M. R13 N.M. N.M. L1 6u8, 60 mΩ, 5.8 A 7x7 mm XPL7030-682ML Coilcraft 6.8 μF D1 Schottky, 40 V, 1 A DO216-AA STPS1L40M ST STPS1L40M D2 Red LED, 3 mA SMD 0603 Standard D3 Signal Schottky SOD-523 BAS69 N.M. U1 Integrated circuit QFN4x4 LED7707 ST LED7707 J2 PCB pad jumper LED7707 ST LED7707 J8 Header 8 SIL 8 Standard SW1, SW2 Jumper 3 SIL 3 Standard	R4					4.7 Ω
R7 Chip resistor 0.1 W, 1% SMD 0603 Standard 360 kΩ R8 680 kΩ R9, R10 100 kΩ R11 1.2 kΩ R12 N.M. R13 N.M. L1 6u8, 60 mΩ, 5.8 A 7x7 mm XPL7030-682ML Coilcraft 6.8 μF D1 Schottky, 40 V, 1 A DO216-AA STPS1L40M ST STPS1L40M D2 Red LED, 3 mA SMD 0603 Standard D3 Signal Schottky SOD-523 BAS69 N.M. U1 Integrated circuit QFN4x4 LED7707 ST LED7707 J2 PCB pad jumper Standard J8 Header 8 SIL 8 Standard SW1, SW2 Jumper 3 SIL 3 Standard	R5					330 kΩ
R8 R9, R10 R11 R12 R13 R14 R15 R15 R16 R17 R17 R18 R19 R19	R6					24 kΩ
R9, R10 R11 1.2 kΩ N.M.	R7		SMD 0603		Standard	360 kΩ
R11 R12 R12 N.M. R13 L1 608, 60 mΩ, 5.8 A 7x7 mm XPL7030-682ML Coilcraft 6.8 μF D1 Schottky, 40 V, 1 A D0216-AA STPS1L40M ST STPS1L40M D2 Red LED, 3 mA SMD 0603 Standard D3 Signal Schottky SOD-523 BAS69 N.M. U1 Integrated circuit QFN4x4 LED7707 ST LED7707 J2 PCB pad jumper J8 Header 8 SIL 8 Standard SW1, SW2 Jumper 3 SIL 3 Standard N.M.	R8					680 kΩ
R12 N.M. R13 N.M. L1 6u8, 60 mΩ, 5.8 A 7x7 mm XPL7030-682ML Coilcraft 6.8 μF D1 Schottky, 40 V, 1 A DO216-AA STPS1L40M ST STPS1L40M D2 Red LED, 3 mA SMD 0603 Standard D3 Signal Schottky SOD-523 BAS69 N.M. U1 Integrated circuit QFN4x4 LED7707 ST LED7707 J2 PCB pad jumper SIL 8 Standard SW1, SW2 Jumper 3 SIL 3 Standard	R9, R10					100 kΩ
R13 N.M. L1 6u8, 60 mΩ, 5.8 A 7x7 mm XPL7030-682ML Coilcraft 6.8 μF D1 Schottky, 40 V, 1 A DO216-AA STPS1L40M ST STPS1L40M D2 Red LED, 3 mA SMD 0603 Standard Standard D3 Signal Schottky SOD-523 BAS69 N.M. U1 Integrated circuit QFN4x4 LED7707 ST LED7707 J2 PCB pad jumper Standard Standard SW1, SW2 Jumper 3 SIL 3 Standard	R11					1.2 kΩ
L1 6u8, 60 mΩ, 5.8 A 7x7 mm XPL7030-682ML Coilcraft 6.8 μF D1 Schottky, 40 V, 1 A DO216-AA STPS1L40M ST STPS1L40M D2 Red LED, 3 mA SMD 0603 Standard D3 Signal Schottky SOD-523 BAS69 N.M. U1 Integrated circuit QFN4x4 LED7707 ST LED7707 J2 PCB pad jumper SIL 8 Standard SW1, SW2 Jumper 3 SIL 3 Standard	R12					N.M.
D1 Schottky, 40 V, 1 A DO216-AA STPS1L40M ST STPS1L40M D2 Red LED, 3 mA SMD 0603 Standard D3 Signal Schottky SOD-523 BAS69 N.M. U1 Integrated circuit QFN4x4 LED7707 ST LED7707 J2 PCB pad jumper Standard Standard SW1, SW2 Jumper 3 SIL 3 Standard	R13					N.M.
D2 Red LED, 3 mA SMD 0603 Standard D3 Signal Schottky SOD-523 BAS69 N.M. U1 Integrated circuit QFN4x4 LED7707 ST LED7707 J2 PCB pad jumper Standard Standard SW1, SW2 Jumper 3 SIL 3 Standard	L1	6u8, 60 mΩ, 5.8 A	7x7 mm	XPL7030-682ML	Coilcraft	6.8 µF
D3 Signal Schottky SOD-523 BAS69 N.M. U1 Integrated circuit QFN4x4 LED7707 ST LED7707 J2 PCB pad jumper J8 Header 8 SIL 8 Standard SW1, SW2 Jumper 3 SIL 3 Standard	D1	Schottky, 40 V, 1 A	DO216-AA	STPS1L40M	ST	STPS1L40M
U1 Integrated circuit QFN4x4 LED7707 ST LED7707 J2 PCB pad jumper J8 Header 8 SIL 8 Standard SW1, SW2 Jumper 3 SIL 3 Standard	D2	Red LED, 3 mA	SMD 0603		Standard	
J2 PCB pad jumper J8 Header 8 SIL 8 Standard SW1, SW2 Jumper 3 SIL 3 Standard	D3	Signal Schottky	SOD-523		BAS69	N.M.
J8 Header 8 SIL 8 Standard SW1, SW2 Jumper 3 SIL 3 Standard	U1	Integrated circuit	QFN4x4	LED7707	ST	LED7707
SW1, SW2 Jumper 3 SIL 3 Standard	J2	PCB pad jumper				
	J8	Header 8	SIL 8		Standard	
SW3 Push button 6x6 mm FSM4JSMAT TYCO	SW1, SW2	Jumper 3	SIL 3		Standard	
	SW3	Push button	6x6 mm	FSM4JSMAT	TYCO	

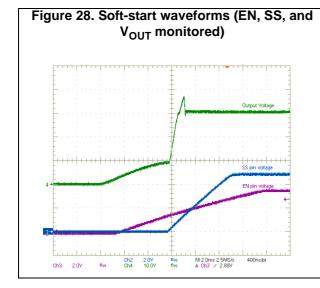
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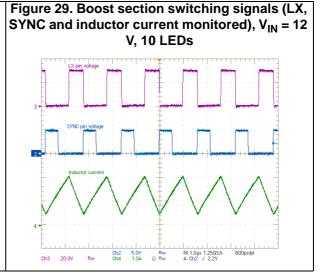


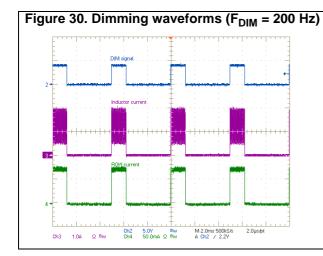
7 Electrical characteristics

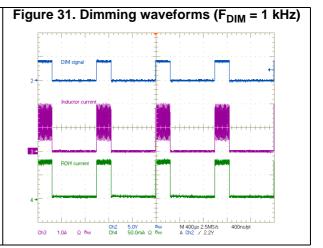












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LED7707 Package information

8 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK[®] packages, depending on their level of environmental compliance. ECOPACK[®] specifications, grade definitions and product status are available at: www.st.com. ECOPACK[®] is an ST trademark.

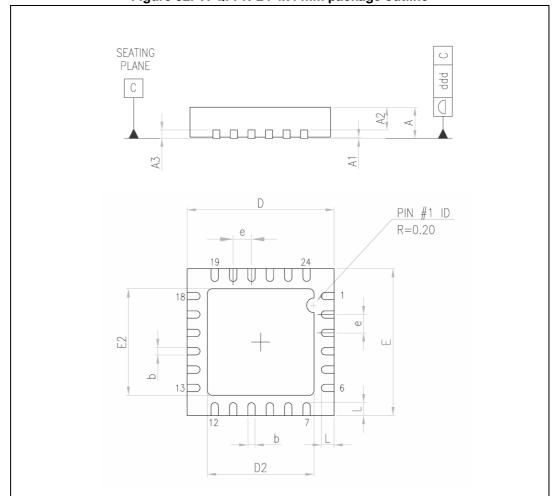


Figure 32. VFQFPN-24 4x4 mm package outline

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Package information LED7707

Table 10. VFQFPN-24 4x4 mm mechanical data

Dim.	mm			
Dilli.	Min.	Тур.	Max.	
А	0.80	0.90	1.00	
A1	0.00	0.02	0.05	
A3		0.20		
b	0.18	0.25	0.30	
D	3.85	4.00	4.15	
D2	2.40	2.50	2.60	
E	3.85	4.00	4.15	
E2	2.40	2.50	2.60	
е		0.50		
L	0.30	0.40	0.50	
ddd			0.08	

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LED7707 Revision history

9 Revision history

Table 11. Document revision history

Date	Revision	Changes
18-Sep-2008	1	Initial release.
20-Oct-2008	2	Updated <i>Table 3</i> and <i>Table 5</i> . Removed <i>Table 4</i> .
10-Apr-2009	3	Updated <i>Table 4</i> , <i>Table 5</i> , <i>Figure 3</i> , <i>Figure 4</i> , <i>Figure 8</i> , <i>Figure 9</i> and <i>Table 9</i> .
11-Sep-2018	4	Updated Section 5.2.1: Current generators. Minor text changes.
15-Oct-2018	5	Updated Section 5.2.2: PWM dimming.



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